

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,084,455 B2
APPLICATION NO. : 10/770045
DATED : August 1, 2006
INVENTOR(S) : Richard A. Blanchard

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page, item [57]

Abstract, line 18, after "the", change "another" to --other--.

Col. 3, line 12, begin a new paragraph and add

--Accordingly, it would be desirable to provide a method of fabricating the MOSFET structure shown in FIG. 3 that requires a minimum number of epitaxial deposition steps so that it can be produced less expensively while also allowing sufficient control of process parameters so that a high degree of charge compensation can be achieved in adjacent columns of opposite doping type in the drift region of the device.--

Col. 3, line 33, after "the", change "another" to --other--.

Col. 5, line 9, after "layer", change "502" to --501--.

Col. 5, line 17, after "trench", change "5201" to --520₁--.

Col. 5, line 25, after "layer", change "524," to --524₁--.

Col. 6, line 31, after "encompasses", delete --a--.

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,084,455 B2
APPLICATION NO. : 10/770045
DATED : August 1, 2006
INVENTOR(S) : Richard A. Blanchard

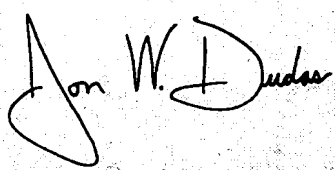
Page 2 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 6, line 39, after first word "The", change "polysilcon" to --polysilicon--.

Signed and Sealed this

Thirteenth Day of November, 2007

A handwritten signature in black ink, reading "Jon W. Dudas". The signature is written in a cursive style with a large, looped initial "J".

JON W. DUDAS
Director of the United States Patent and Trademark Office